

PUA3210 (PU3210)

Silicon PNP epitaxial planar type

For power amplification

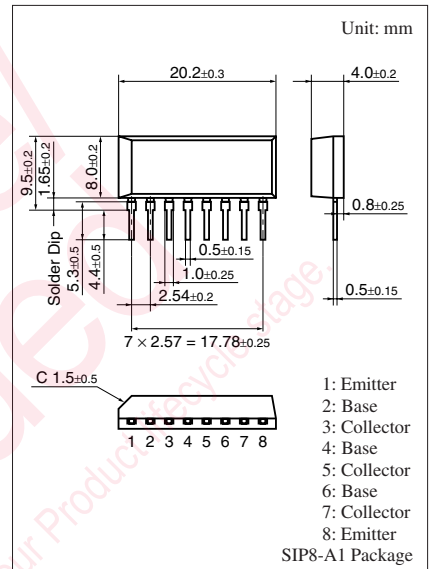
Complementary to PUA3110 (PU3110)

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- PNP 3 elements

■ Absolute Maximum Ratings $T_C = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-60	V
Collector-emitter voltage (Base open)	V_{CEO}	-60	V
Emitter-base voltage (Collector open)	V_{EBO}	-6	V
Collector current	I_C	-3	A
Peak collector current	I_{CP}	-5	A
Base current	I_B	-1	A
Collector power dissipation	P_C	15	W
		$T_a = 25^\circ C$	
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

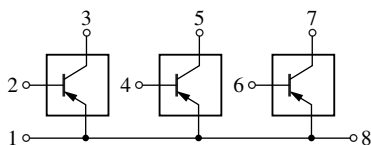


■ Electrical Characteristics $T_C = 25^\circ C \pm 3^\circ C$

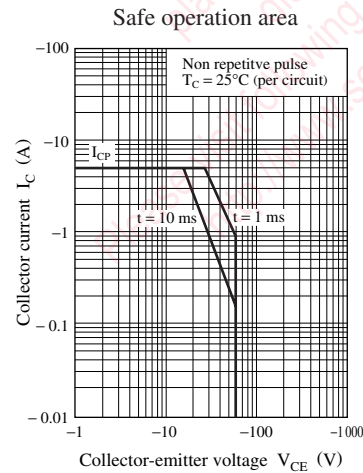
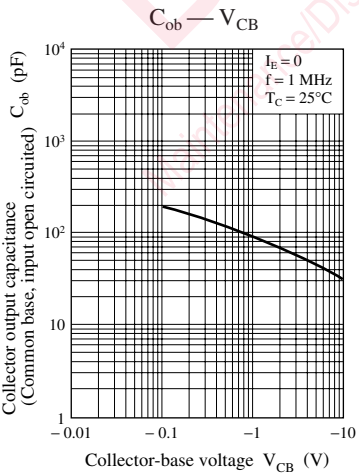
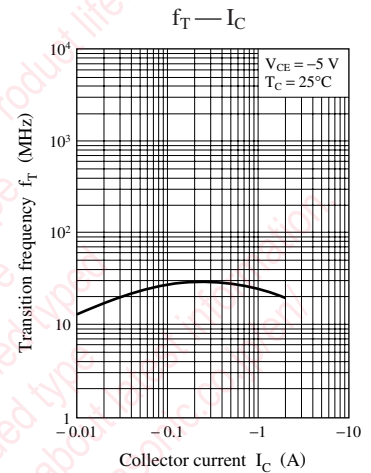
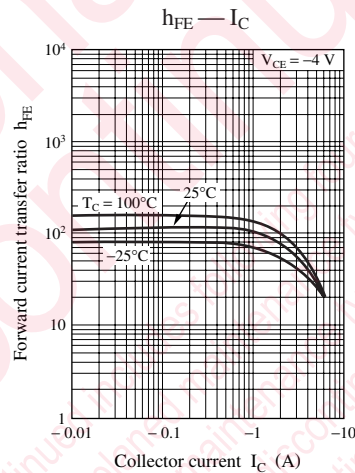
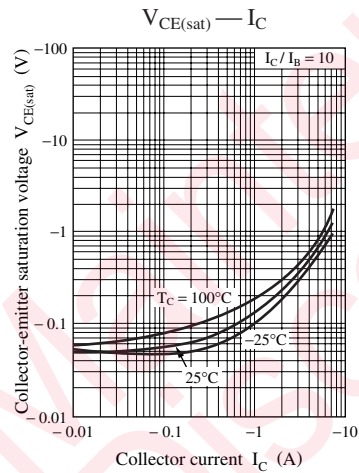
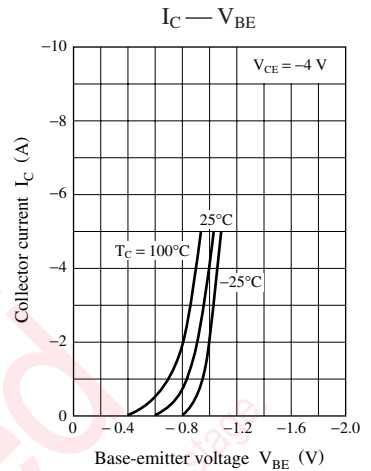
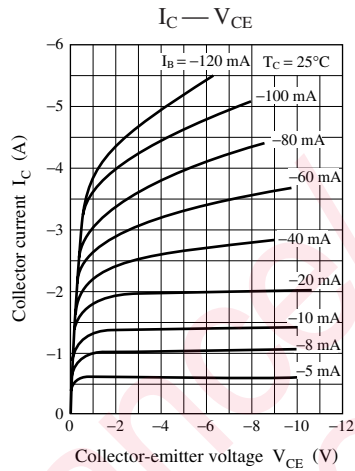
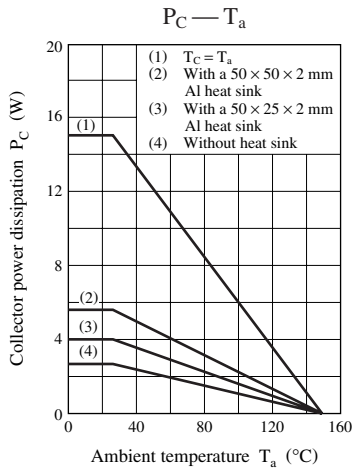
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -30 \text{ mA}, I_B = 0$	-60			V
Base-emitter saturation voltage	V_{BE}	$V_{CE} = -4 \text{ V}, I_C = -3 \text{ A}$			-1.8	V
Collector-emitter cutoff current ($V_{BE} = 0$)	I_{CES}	$V_{CE} = -60 \text{ V}, V_{BE} = 0$			-200	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -30 \text{ V}, I_B = 0$			-300	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -4 \text{ V}, I_C = -1 \text{ A}$	70		250	—
	h_{FE2}	$V_{CE} = -4 \text{ V}, I_C = -3 \text{ A}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3 \text{ A}, I_B = -0.375 \text{ A}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -1 \text{ A}$		0.5		μs
Storage time	t_{stg}	$I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		1.2		μs
Fall time	t_f	$V_{CC} = -50 \text{ V}$		0.3		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

■ Internal Connection



Note) The part number in the parenthesis shows conventional part number.



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